

RF AMPLIFIER

MODEL *TM3019*

Available as: TM3019, 4 Pin TO-8 (T4)
 TN3019, 4 Pin Surface Mount (SM3)
 BX3019, Connectorized Housing (H1)

Features

- GaAs FET Amplifier
- High Output Power: +22 dBm Typical
- Operating Temp. - 30 °C to + 71 °C
- Environmental Screening Available

Specifications

CHARACTERISTIC	TYPICAL Ta= 25 °C	MIN/MAX Ta = -30 °C to +71 °C
Frequency	500 - 1300 MHz	500 - 1300 MHz
Gain (dB)	13.5	12.5 Min.
Power @ 1 dB Comp. (dBm)	+22	+21 Min.
Reverse Isolation (dB)	-21.5	-20 Max.
VSWR In	<1.75:1	2.2:1 Max.
Out	<1.5:1	2.0:1 Max.
Noise Figure (dB)	2.2	3.0 Max.
Power Vdc	+15	+15
mA	105	110 Max.

Note: Care should always be taken to effectively ground the case of each unit.

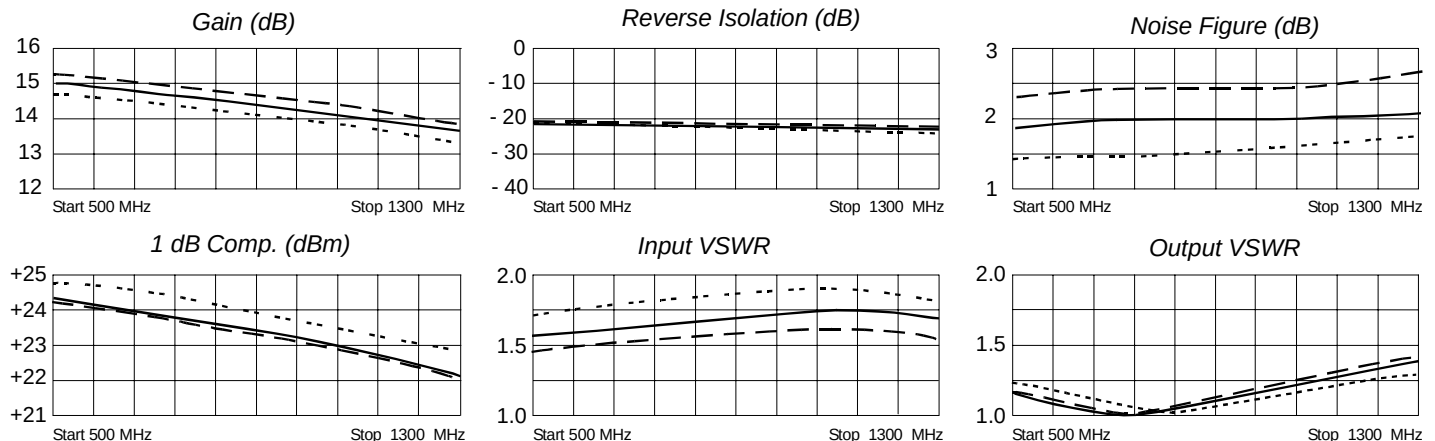
Typical Intermodulation Performance at 25 ° C

Second Order Harmonic Intercept Point +55 dBm (Typ.)
 Second Order Two Tone Intercept Point +50 dBm (Typ.)
 Third Order Two Tone Intercept Point +36 dBm (Typ.)

Maximum Ratings

Ambient Operating Temperature -55°C to + 100 °C
 Storage Temperature -62°C to + 125 °C
 Case Temperature + 125 °C
 DC Voltage + 18 Volts
 Continuous RF Input Power + 20 dBm
 Short Term RF Input Power 200 Milliwatts (1 Minute Max.)
 Maximum Peak Power 0.5 Watt (3 µsec Max.)

Typical Performance Data



Legend ——— + 25 °C - - - - + 71 °C -30 °C